Vishay Semiconductors

INT-A-PAK Power Modules Ultrafast Diodes, 300 A

INT-A-PAK	

PRODUCT SUMMARY	
$I_{F(AV)}$ at T_C	300 A at 48 °C
V _R	600 V
t _{rr} (typical)	130 ns
I _{F(DC)} at T _C	230 A at 100 °C

FEATURES

- Electrically insulated by DBC ceramic
- 3500 V_{RMS} isolating voltage
- Standard JEDEC package
- Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- UL approved file E78996
- Case style INT-A-PAK
- Compliant to RoHS directive 2002/95/EC
- Designed and gualified for industrial level

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		600	V		
Continuous forward ourrent per log		T _C = 25 °C	435			
Continuous forward current per leg	I _F	T _C = 100 °C	230	А		
Single pulse forward current	I _{FSM}	Limited by junction temperature	TBD			
Maximum power dissipation per leg	Р	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$	781	w		
Maximum power dissipation per leg	PD	T _C = 100 °C	313	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		- 40 to 150	°C		
RMS insulation voltage	V _{INS}	50 Hz, circuit to base, all terminals shorted, t = 1 s	3500 V			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX. U		UNITS				
Cathode to anode breakdown voltage	V_{BR}	I _R = 500 μA	600	-	-			
		I _F = 150 A	-	1.23	1.53			
Forward valtage drep per lag		V	V	M	I _F = 300 A	-	1.43	1.96
Forward voltage drop per leg	V_{FM}	I _F = 150 A, T _J = 125 °C	-	1.11	1.29			
		I _F = 300 A, T _J = 125 °C	-	1.39	1.73			
Maximum reverse leakage current	I _{RM}	$T_J = 150 \ ^{\circ}C, \ V_R = 600 \ V$	-	-	50	mA		







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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	+	T _J = 25 °C		-	130	165	ns	
Reverse recovery time	t _{rr}	T _J = 125 °C		-	195	260		
Peak recovery current	1	$T_J = 25 \text{ °C}$ $I_F = 50 \text{ A}$	T _J = 25 °C	I _F = 50 A	-	11	18	•
Feak recovery current	Irr	T _J = 125 °C	dl/dt = 200 A/µs V _R = 400 V (per leg)	-	20	30	A	
Reverse recovery charge	0	T _J = 25 °C		-	670	1485	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1800	3900	no	
Peak rate of recovery current	dl _{(rec)M} /dt	T _J = 125 °C		-	-	400	A/µs	
Softnana factor por log		$I_F = 50 \text{ A}, \text{ T}_J = 25 \text{ °C}, \text{ dI}$	/dt = 400 A/µs, V _R = 200 V	-	0.2	-		
Softness factor per leg	S	$I_F = 50 \text{ A}, T_J = 125 \text{ °C}, \text{ dI/dt} = 400 \text{ A/}\mu\text{s}, \text{ V}_R = 200 \text{ V} \qquad - \qquad 0.22 \qquad -$			-			

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction op storage temperature	0	T _J , T _{Stg}		- 40 to 150	°C	
Maximum thermal res junction to case per l	B _{thic} DC operation		0.16			
Typical thermal resist case to heatsink	tance,	R _{thCS}	Mounting surface, flat, smooth and greased	0.05	K/W	
Mounting	to heatsink	-	A mounting compound is recommended and the torgue should be rechecked after a period of	4 to 6	Nm	
torque ± 10 %	busbar		3 hours to allow the spread of the compound.			
Approvimate weight				200	g	
Approximate weight				7.1	oz.	
Case style				INT-A-	PAK	



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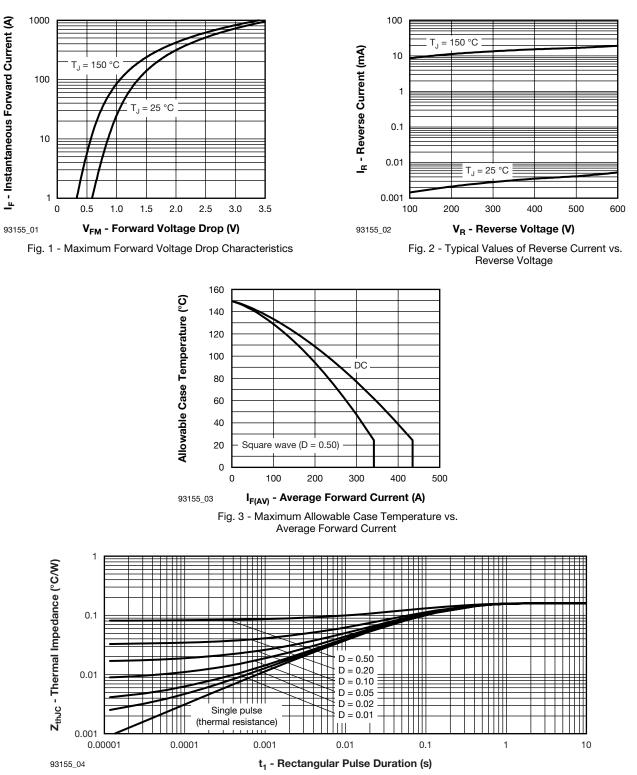


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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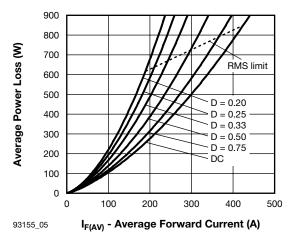


Fig. 5 - Forward Power Loss Characteristics

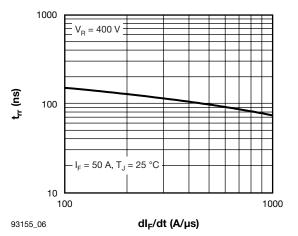
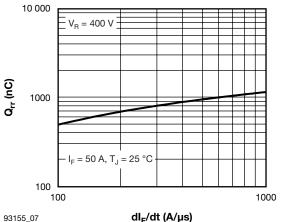


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)



dl_F/dt (A/µs)

Fig. 7 - Typical Reverse Recovery Charge vs. dl_F/dt (Per Leg)

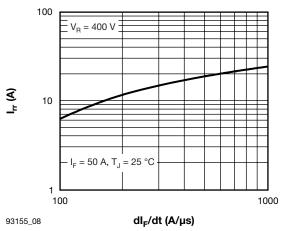


Fig. 8 - Typical Reverse Recovery Current vs. dl_F/dt (Per Leg)

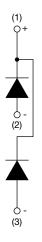


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ORDERING INFORMATION TABLE

Device code	VSK	С	U	300	1	06	PbF
	1	2	3	4		5	6
	1 - 2 -	Circ	dule type cuit confi 2 diode	guratior		ode	
	3 -	U =	Ultrafas	t diode			
	4 -	Cur	rent ratii	ng (300	= 300 A	N)	
	5 -	Volt	age rati	ng (06 =	600 V)		
	6 -	PbF	= Lead	(Pb)-fre	e		

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95254				

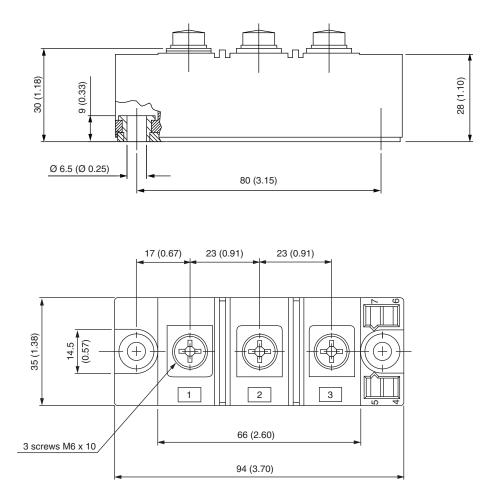


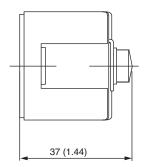
Outline Dimensions

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INT-A-PAK DBC

DIMENSIONS in millimeters (inches)







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